TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155190

ULTRA HIGH SPEED SWITCHING APPLICATION.

• Small Package : SC-59

• Low Forward Voltage : V_{F(3)}=0.92V (Typ.)

• Fast Reverse Recovery Time: trr=1.6ns (Typ.)

• Small Total Capacitance : C_T=2.2pF (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	v_{RM}	85	V
Reverse Voltage	$V_{\mathbf{R}}$	80	V
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	IO	100	mA
Surge Current (10ms)	I_{FSM}	2	Α
Power Dissipation	P	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

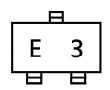
Unit in mm +0.5 2.5 - 0.3 +0.25 1.5 - 0.15 1.5 - 0.15 2.6 - 0.25 1.5 - 0.15 2.5 - 0.3 40.25 1.5 - 0.15 1.5 - 0.15 2.5 - 0.3 1.5 - 0.15 2.5 - 0.3 3 1. N.C. 2. CATHODE 3. ANODE JEDEC TO-236MOD EIAJ SC-59 TOSHIBA 1-3G1C

Weight: 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

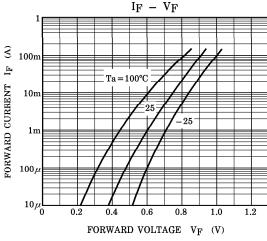
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	$I_{\mathbf{F}} = 1 \text{mA}$	_	0.61	_	v
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$		0.74		
	$V_{F(3)}$	$I_{ m F}\!=\!100{ m mA}$	_	0.92	1.20	
neverse Current	I _{R (1)}	$V_R=30V$	_	_	0.1	μ A
	$I_{R(2)}$	$V_R = 80V$	_	_	0.5	
Total Capacitance	C_{T}	$V_R=0$, $f=1MHz$	_	2.2	4.0	pF
Reverse Recovery Time	${ m t_{rr}}$	I _F =10mA (Fig.1)		1.6	4.0	ns

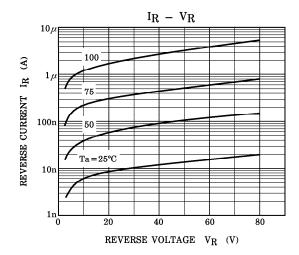
MARKING

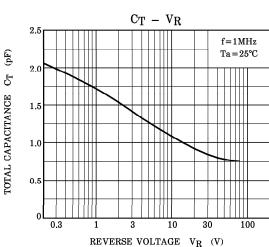


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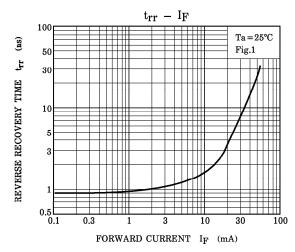
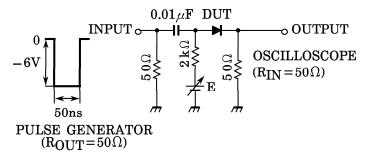
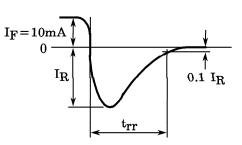


Fig.1 Reverse recovery time (t_{rr}) test circuit

INPUT WAVEFORM

OUTPUT WAVEFORM





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